0.75-Ω SPDT ANALOG SWITCH WITH INPUT LOGIC TRANSLATION

Check for Samples: TS5A6542

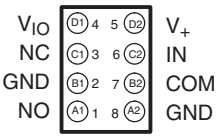
FEATURES

- **Specified Break-Before-Make Switching**
- **Low ON-State Resistance (0.75 Ω Max)**
- **Control Inputs Referenced to V_{IO}**
- **Low Charge Injection**
- **Excellent ON-State Resistance Matching**
- **Low Total Harmonic Distortion (THD)**
- **2.25-V to 5.5-V Power Supply (V_+)**
- **1.65-V to 1.95-V Logic Supply (V_{IO})**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **4000-V Human-Body Model (A114-B, Class II)**
  - **1000-V Charged-Device Model (C101)**
  - **400-V Machine Model (A115-A)**
- **COM Port to GND**
  - **8000-V Human-Body Model (A114-B, Class II)**
  - **±15-kV Contact Discharge (IEC 61000-4-2)**

APPLICATIONS

- **Cell Phones**
- **PDAs**
- **Portable Instrumentation**

YZP PACKAGE
(BOTTOM VIEW)



DESCRIPTION/ORDERING INFORMATION

The TS5A6542 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device offers a low ON-state resistance with an excellent channel-to-channel ON-state resistance matching, and the break-before-make feature to prevent signal distorion during the transferring of a signal from one path to another. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

The TS5A6542 has a separate logic supply pin (V_{IO}) that is characterized to operate from 1.65 V to 1.95 V. V_{IO} powers the control circuitry, which allows the TS5A6542 to be controlled by 1.8-V signals.

Table 1. ORDERING INFORMATION(1)

T_A	PACKAGE(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING(3)
–40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A6542YZPR	_ _ _ JH7

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
(3) YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the wafer fab/assembly site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

SUMMARY OF CHARACTERISTICS(1)

Configuration	2:1 Multiplexer/Demultiplexer (1 × SPDT)
Number of channels	1
ON-state resistance (r_{on})	0.75 Ω max
ON-state resistance match (Δr_{on})	0.1 Ω max
ON-state resistance flatness ($r_{on(flat)}$)	0.1 Ω max
Turn-on/turn-off time (t_{ON}/t_{OFF})	25 ns/20 ns
Charge injection (Q_C)	15 pC
Bandwidth (BW)	43 MHz
OFF isolation (O_{ISO})	–63 dB at 1 MHz
Crosstalk (X_{TALK})	–63 dB at 1 MHz
Total harmonic distortion (THD)	0.004%
Leakage current ($I_{NO(OFF)}/I_{NC(OFF)}$)	20 nA
Package option	8-pin WCSP

(1) V_+ = 5 V, T_A = 25°C

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

ABSOLUTE MAXIMUM RATINGS(1) (2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_+ V_{IO}	Supply voltage range(3)		–0.5	6.5	V
V_{NC} V_{NO} V_{COM}	Analog voltage range(3) (4) (5)		–0.5	V_+ + 0.5	V
$I_{I/OK}$	Analog port diode current(6)	V_{NO}, V_{COM} < 0 or V_{NO}, V_{COM} > V_+	–50	50	mA
I_{NC} I_{NO} I_{COM}	On-state switch current	$V_{NO,}$ V_{COM} = 0 to V_+	–450	450	mA
	On-state peak switch current(7)		–700	700	
V_I	Digital input voltage range(3) (4)		–0.5	6.5	V
I_{IK}	Digital input clamp current	V_I < 0	–50		mA
I_+ I_{GND}	Continuous current through V_+ or GND		–100	100	mA
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(3) All voltages are with respect to ground, unless otherwise specified.
(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(5) This value is limited to 5.5 V maximum.
(6) Requires clamp diodes on analog port to V_+
(7) Pulse at 1-ms duration < 10% duty cycle

THERMAL IMPEDANCE RATINGS

				UNIT
θ_{JA}	Package thermal impedance(1)	YZP package	102	°C/W

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY(1)

V_+ = 4.5 V to 5.5 V, V_{IO} = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch								
Analog signal range	V_{COM}, V_{NO}				0		V_+	V
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 2.5 V, I_{COM} = –100 mA, Switch ON, See Figure 14	25°C	4.5 V		0.5	0.75	Ω
			Full				0.8	
ON-state resistance match between channels	Δr_{on}	V_{NO} or V_{NC} = 2.5 V, I_{COM} = –100 mA, Switch ON, See Figure 14	25°C	4.5 V		0.05	0.1	Ω
			Full				0.1	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA, Switch ON, See Figure 14	25°C	4.5 V		0.1		Ω
		V_{NO} or V_{NC} = 1 V, 1.5 V, 2.5 V, I_{COM} = –100 mA, Switch ON, See Figure 14	25°C			0.1	0.25	
			Full				0.25	
NO, NC OFF leakage current	$I_{NO(OFF)}$, $I_{NC(OFF)}$	V_{NO} = 1 V, 4.5 V, V_{COM} = 4.5 V, 1 V, V_{NC} = Open, or V_{NC} = 1 V, 4.5 V, V_{COM} = 4.5 V, 1 V, V_{NO} = Open, Switch OFF, See Figure 15	25°C	5.5 V	–20	2	20	nA
			Full		–100		100	
NC, NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 1 V, 4.5 V, V_{COM}, V_{NC} = Open, or V_{NC} = 1 V, 4.5 V, V_{COM}, V_{NO} = Open, Switch ON, See Figure 16	25°C	5.5 V	–20	2	20	nA
			Full		–200		200	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, 4.5 V, V_{NO} and V_{NC} = Open, or V_{COM} = 1 V, 4.5 V, V_{NO} or V_{NC} = Open, See Figure 16	25°C	5.5 V	–20	2	20	nA
			Full		–200		200	
Digital Control Input (IN)(2)								
Input logic high	V_{IH}	V_{IO} = 1.65 V to 1.95 V	Full		0.65 × V_{IO}		V_{IO}	V
Input logic low	V_{IL}	V_{IO} = 1.65 V to 1.95 V	Full		0		0.35 × V_{IO}	V
Input leakage current	I_{IH}, I_{IL}	V_I = V_{IO} or 0	25°C	5.5 V	–2		2	nA
			Full		–20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY (1) (continued)

V_+ = 4.5 V to 5.5 V, V_{IO} = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L= 35 pF, See Figure 18	25°C	5 V	1	12.5	25	ns
				Full	4.5 V			30	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	5 V	1	9.5	20	ns
				Full	4.5 V			25	
Break-before-make time	t_{BBM}	V_{NC} = V_{NO} = V_+/2, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	5 V	1	5	10	ns
				Full	4.5 V	1		12	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 23	25°C	5 V		15		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 17	25°C	5 V		37		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND, Switch ON,	See Figure 17	25°C	5 V		130		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 17	25°C	5 V		130		pF
Digital input capacitance	C_I	V_I = V_{IO} or GND,	See Figure 17	25°C	5 V		6.5		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 20	25°C	5 V		43		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	See Figure 21	25°C	5 V		–63		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	See Figure 22	25°C	5 V		–63		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 24	25°C	5 V		0.004		%
Supply									
Positive supply current	I_+	V_I = V_{IO} or GND		25°C	5.5 V		5.5	100	nA
				Full				750	

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY(1)

V_+ = 3 V to 3.6 V, V_{IO} = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 2 V, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C	3 V		0.75	0.9	Ω
				Full				1.2	
ON-state resistance match between channels	Δr_{on}	V_{NO} or V_{NC} = 2 V, 0.8 V, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C	3 V		0.1	0.15	Ω
				Full				0.15	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C	3 V		0.2		Ω
		V_{NO} or V_{NC} = 0.8 V, 2 V, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C			0.1	0.3	
				Full				0.3	
NO, NC OFF leakage current	$I_{NO(OFF)}$, $I_{NC(OFF)}$	V_{NO} = 1 V, 3 V, V_{COM} = 3 V, 1 V, V_{NC} = Open, or V_{NC} = 1 V, 3 V, V_{COM} = 3 V, 1 V, V_{NO} = Open,	Switch OFF, See Figure 15	25°C	3.6 V	–20	2	20	nA
				Full		–50		50	
NC, NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 1 V, 3 V, V_{NC} and V_{COM} = Open, or V_{NC} = 1 V, 3 V, V_{NO} and V_{COM} = Open,	Switch ON, See Figure 16	25°C	3.6 V	–10	2	10	nA
				Full		–30		30	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NO} and V_{NC} = Open, or V_{COM} = 3 V, V_{NO} and V_{NC} = Open,	See Figure 16	25°C	3.6 V	–10	2	10	nA
				Full		–30		30	
Digital Control Input (IN)(2)									
Input logic high	V_{IH}	V_{IO} = 1.65 V to 1.95 V		Full		0.65 × V_{IO}		V_{IO}	V
Input logic low	V_{IL}	V_{IO} = 1.65 V to 1.95 V		Full		0		0.35 × V_{IO}	V
Input leakage current	I_{IH}, I_{IL}	V_I = V_{IO} or 0		25°C	3.6 V	–2		2	nA
				Full		–20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY (1) (continued)

V_+ = 3 V to 3.6 V, V_{IO} = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L= 35 pF, See Figure 18	25°C	3.3 V	5	15	30	ns
				Full	3 V	3		35	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	3.3 V	1	9	20	ns
				Full	3 V	1		25	
Break-before-make time	t_{BBM}	V_{NC} = V_{NO} = V_+/2, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	3.3 V	1	8	13	ns
				Full	3 V	1		15	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 23	25°C	3.3V		6.5		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 17	25°C	3.3 V		38		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND, Switch ON,	See Figure 17	25°C	3.3 V		133		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 17	25°C	3.3 V		133		pF
Digital input capacitance	C_I	V_I = V_{IO} or GND,	See Figure 17	25°C	3.3 V		6.5		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 20	25°C	3.3 V		42		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	See Figure 21	25°C	3.3 V		–63		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	See Figure 22	25°C	3.3 V		–63		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 24	25°C	3.3 V		0.004		%
Supply									
Positive supply current	I_+	V_I = V_{IO} or GND		25°C	3.6 V		10	50	nA
				Full				300	

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY(1)

V_+ = 2.25 V to 2.75 V, V_{IO} = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
ON-state resistance	r_{on}	V_{NO} or V_{NC} = 1.8 V, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C	2.25 V		1	1.3	Ω
				Full				1.6	
ON-state resistance match between channels	Δr_{on}	V_{NO} or V_{NC} = 1.8 V, 0.8 V, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C	2.25 V		0.15	0.2	Ω
				Full				0.2	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ (V_{NO} or V_{NC}) ≤ V_+, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C	2.25 V		0.5		Ω
		V_{NO} or V_{NC} = 0.8 V, 1 V, 1.8 V, I_{COM} = –100 mA,	Switch ON, See Figure 14	25°C			0.25	0.5	
				Full				0.6	
NO, NC OFF leakage current	$I_{NO(OFF)}$, $I_{NC(OFF)}$	V_{NO} = 0.5 V, 2.2 V, V_{COM} = 2.2 V, 0.5 V, V_{NC} = Open, or V_{NC} = 0.5 V, 2.2 V, V_{COM} = 2.2 V, 0.5 V, V_{NO} = Open,	Switch OFF, See Figure 15	25°C	2.75 V	–20	2	20	nA
				Full		–50		50	
NC, NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 0.5 V, 2.2 V, V_{NC} and V_{COM} = Open, or V_{NC} = 2.2 V, 0.5 V, V_{NO} and V_{COM} = Open,	Switch ON, See Figure 16	25°C	2.75 V	–10	2	10	nA
				Full		–20		20	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 0.5 V, V_{NO} and V_{NC} = Open, or V_{COM} = 2.2 V, V_{NO} and V_{NC} = Open,	Switch ON, See Figure 16	25°C	2.75 V	–10	2	10	nA
				Full		–20		20	
Digital Control Input (IN)(2)									
Input logic high	V_{IH}	V_{IO} = 1.65 V to 1.95 V		Full		0.65 × V_{IO}		V_{IO}	V
Input logic low	V_{IL}	V_{IO} = 1.65 V to 1.95 V		Full		0		0.35 × V_{IO}	V
Input leakage current	I_{IH}, I_{IL}	V_I = V_{IO} or 0		25°C	2.75 V	–2		2	nA
				Full		–20		20	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{IO} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY (1) (continued)

V_+ = 2.25 V to 2.75 V, V_{IO} = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = V_+, R_L = 50 Ω,	C_L= 35 pF, See Figure 18	25°C	2.5 V	5	20	35	ns
				Full	2.25 V	5		40	
Turn-off time	t_{OFF}	V_{COM} = V_+, R_L = 50 Ω,	C_L = 35 pF, See Figure 18	25°C	2.5 V	2	10	20	ns
				Full	2.25 V	2		25	
Break-before-make time	t_{BBM}	V_{NC} = V_{NO} = V_+/2, R_L = 50 Ω,	C_L = 35 pF, See Figure 19	25°C	2.5 V	1	11	20	ns
				Full	2.25 V	1		25	
Charge injection	Q_C	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, See Figure 23	25°C	2.5 V		5		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 17	25°C	2.5 V		38		pF
NC, NO ON capacitance	$C_{NC(ON)}$, $C_{NO(ON)}$	V_{NC} or V_{NO} = V_+ or GND, Switch ON,	See Figure 17	25°C	2.5 V		135		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 17	25°C	2.5 V		135		pF
Digital input capacitance	C_I	V_I = V_{IO} or GND,	See Figure 17	25°C	2.5 V		6.5		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 20	25°C	2.5 V		40		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 1 MHz,	See Figure 21	25°C	2.5 V		–63		dB
Crosstalk	X_{TALK}	R_L = 50 Ω, f = 1 MHz,	See Figure 22	25°C	2.5 V		–63		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 24	25°C	2.5 V		0.008		%
Supply									
Positive supply current	I_+	V_I = V_{IO} or GND		25°C	2.75 V		10	25	nA
				Full				100	

TYPICAL PERFORMANCE

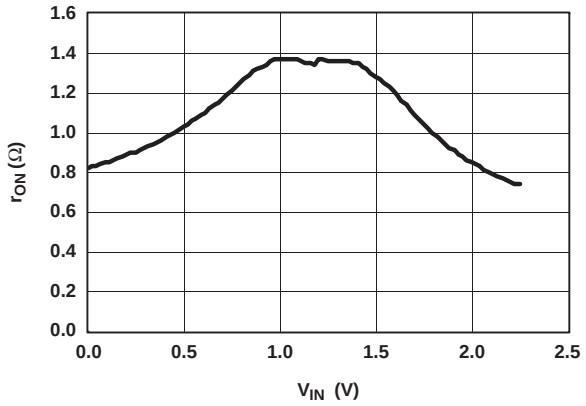


Figure 1. r_{on} vs V_{COM} (V_+ = 2.5 V)

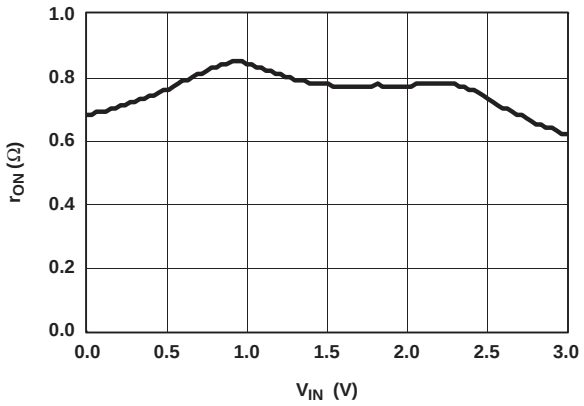


Figure 2. r_{on} vs V_{COM} (V_+ = 3.3 V)

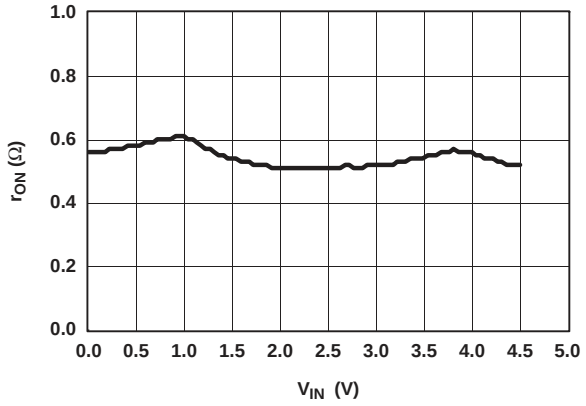


Figure 3. r_{on} vs V_{COM} (V_+ = 5 V)

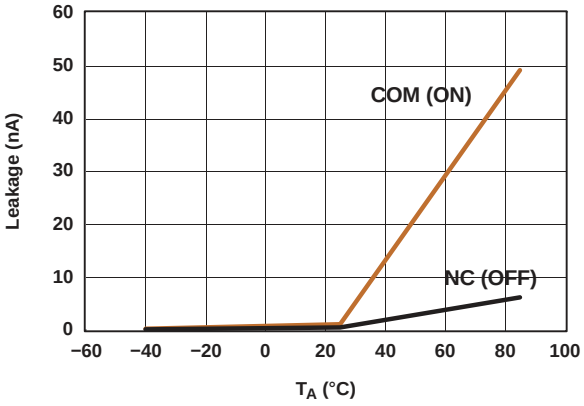


Figure 4. Leakage Current vs Temperature (V_+ = 5 V)

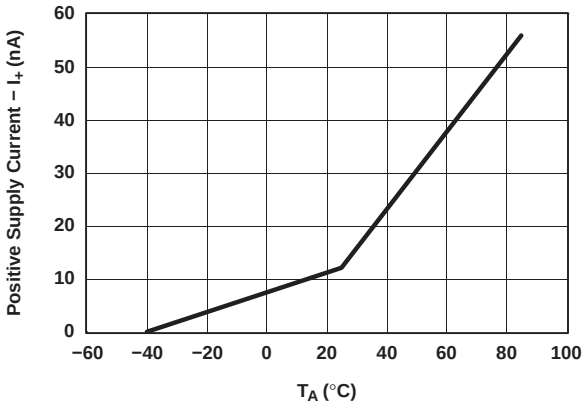


Figure 5. I_+ vs Temperature (V_+ = 5 V)

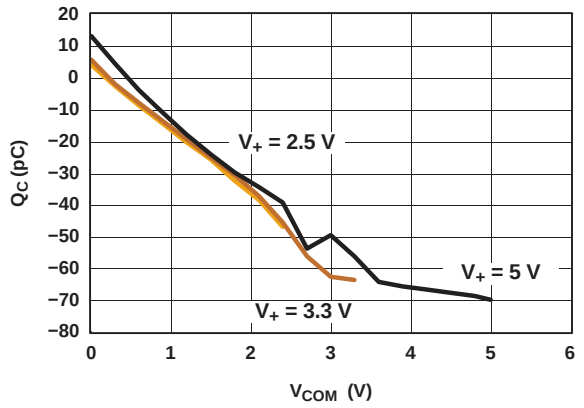


Figure 6. Charge Injection (Q_C) vs V_{COM}

TYPICAL PERFORMANCE (continued)

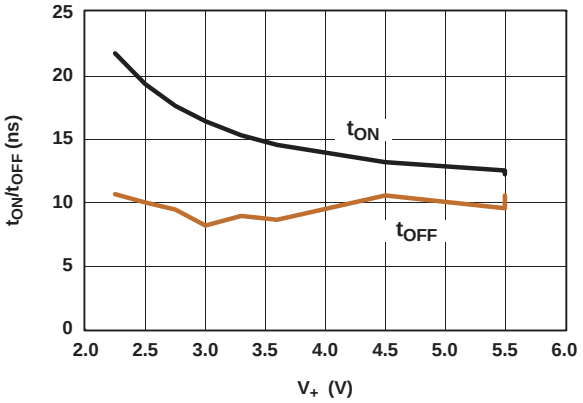


Figure 7. t_{ON}/t_{OFF} vs Supply Voltage

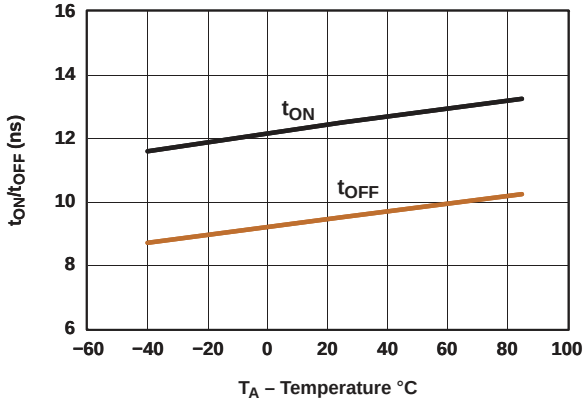


Figure 8. t_{ON}/t_{OFF} vs Temperature (V_+ = 5 V)

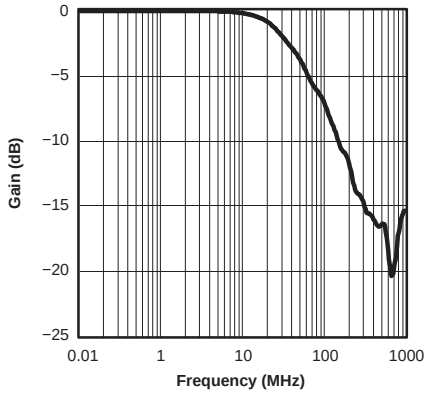


Figure 9. Gain vs Frequency (V_+ = 5 V)

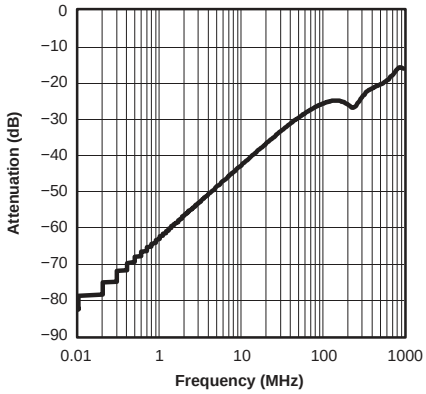


Figure 10. Crosstalk vs Frequency (V_+ = 5 V)

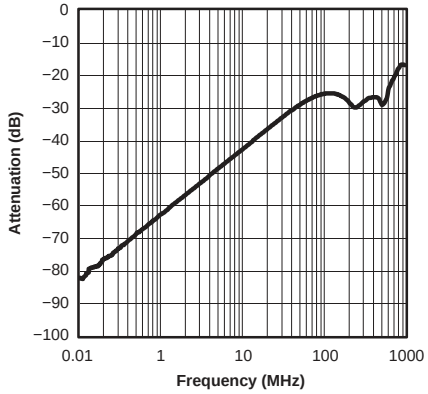


Figure 11. OFF Isolation vs Frequency (V_+ = 5 V)

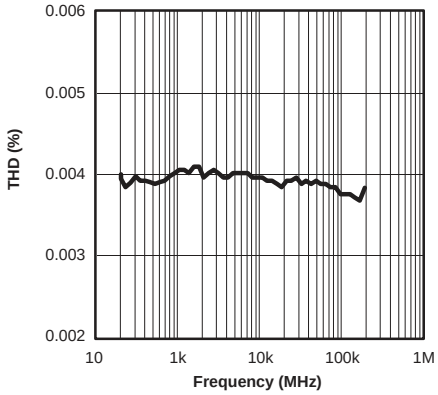


Figure 12. Total Harmonic Distortion vs Frequency (V_+ = 2.5 V)

TYPICAL PERFORMANCE (continued)

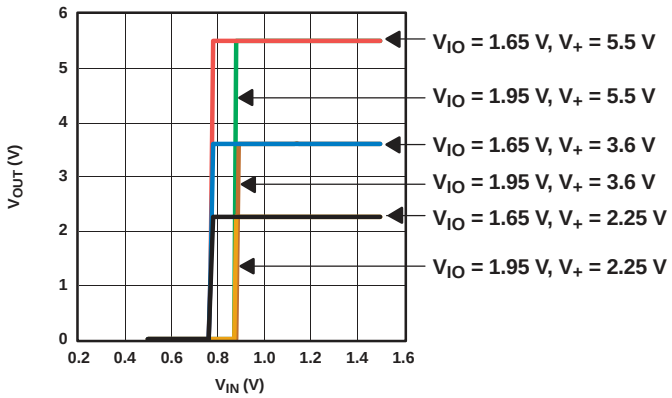


Figure 13. V_{IO} Thresholds

PARAMETER MEASUREMENT INFORMATION

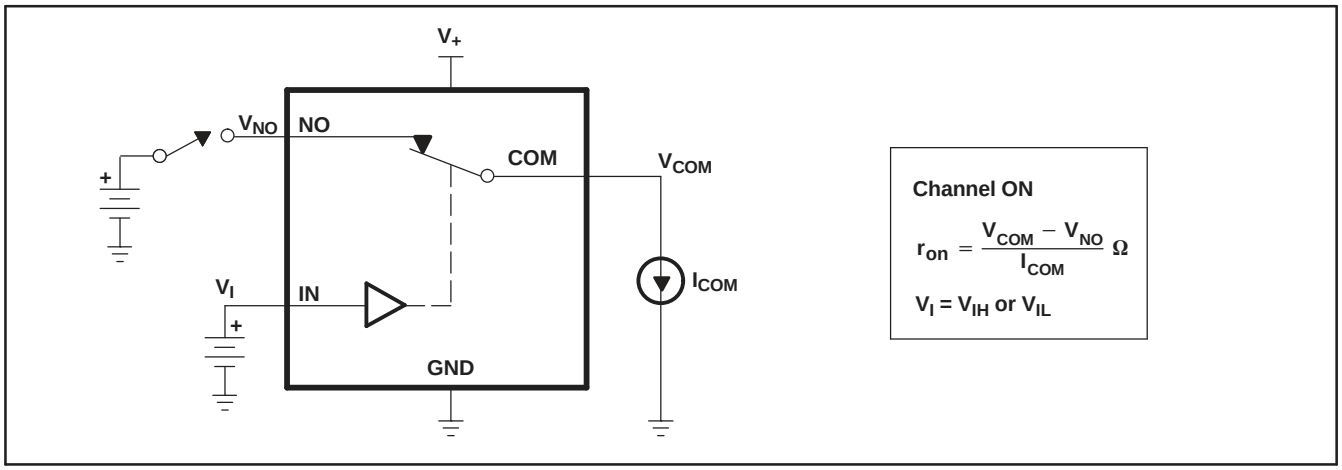


Figure 14. ON-State Resistance (r_{on})

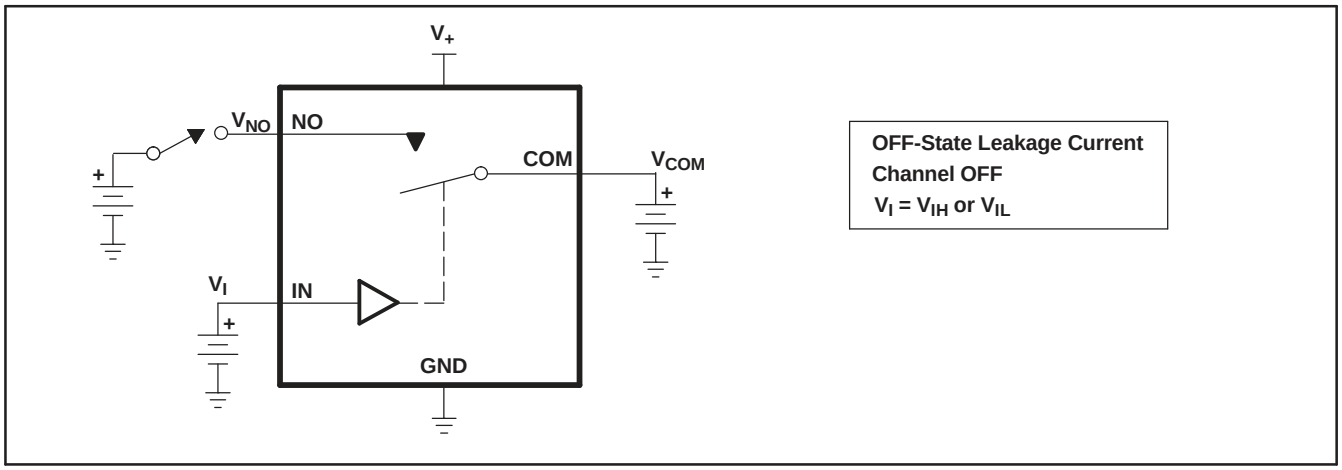


Figure 15. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NC(OFF)}$, $I_{COM(PWROFF)}$, $I_{NC(PWR(FF)}$)

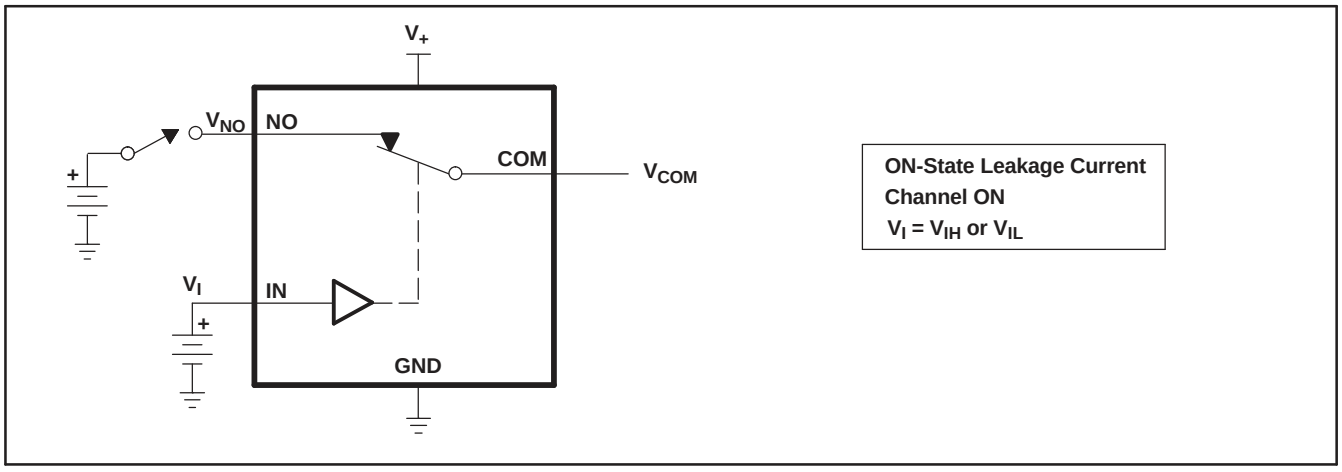


Figure 16. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NC(ON)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

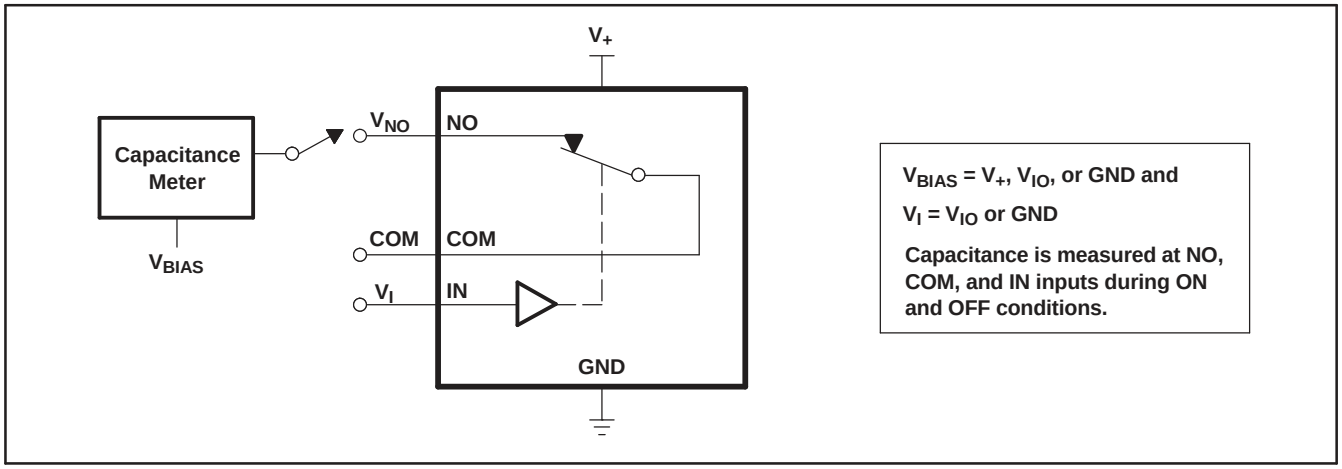
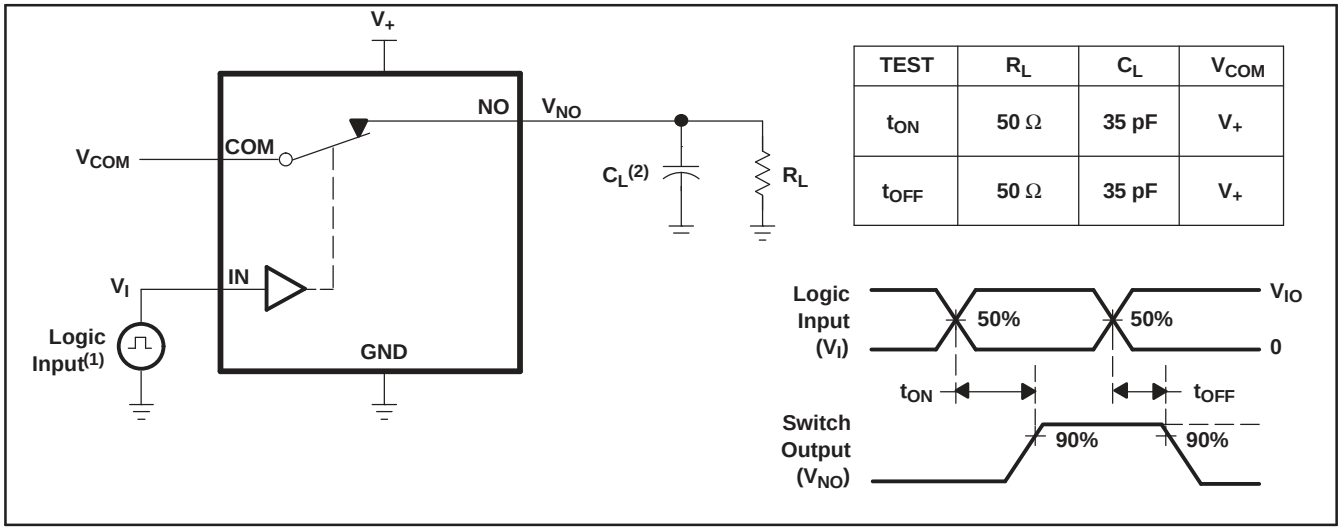


Figure 17. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NC(OFF)}$, $C_{NC(ON)}$)

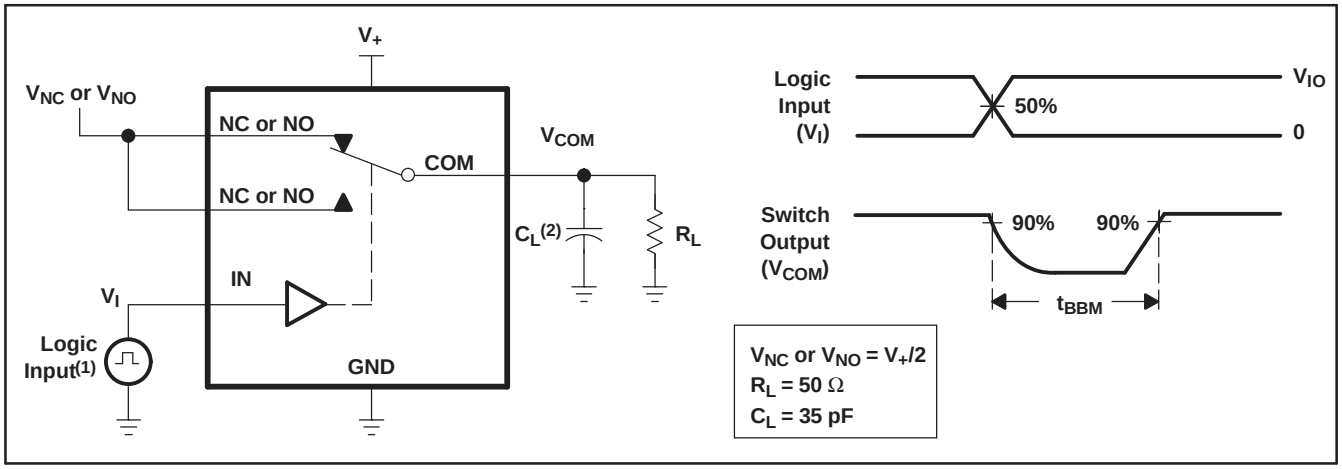


TEST	R_L	C_L	V_{COM}
t_{ON}	50 Ω	35 pF	V_+
t_{OFF}	50 Ω	35 pF	V_+

(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 18. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

PARAMETER MEASUREMENT INFORMATION (continued)



(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 19. Break-Before-Make Time (t_{BBM})

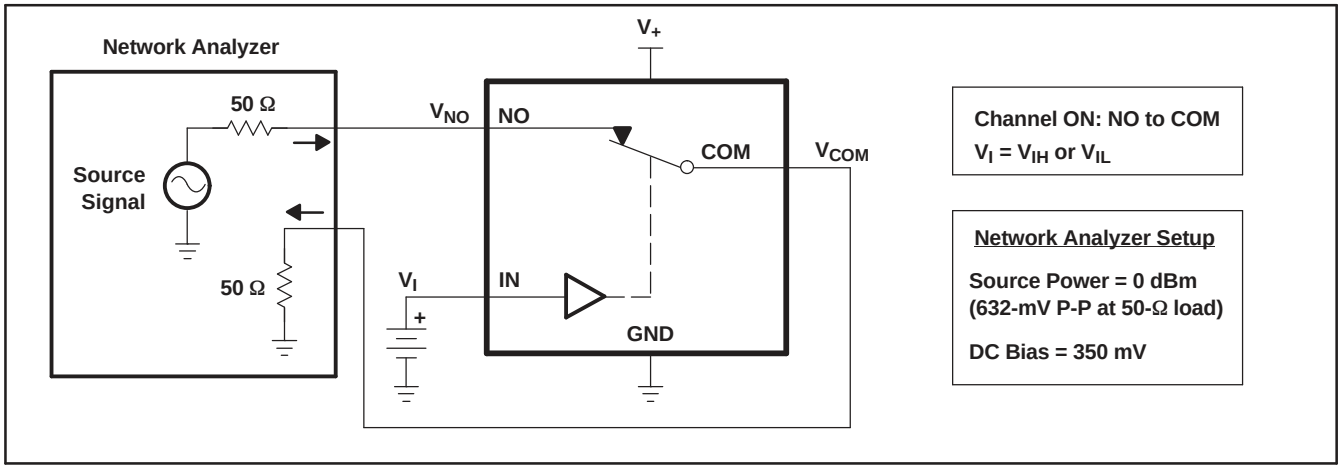


Figure 20. Bandwidth (BW)

PARAMETER MEASUREMENT INFORMATION (continued)

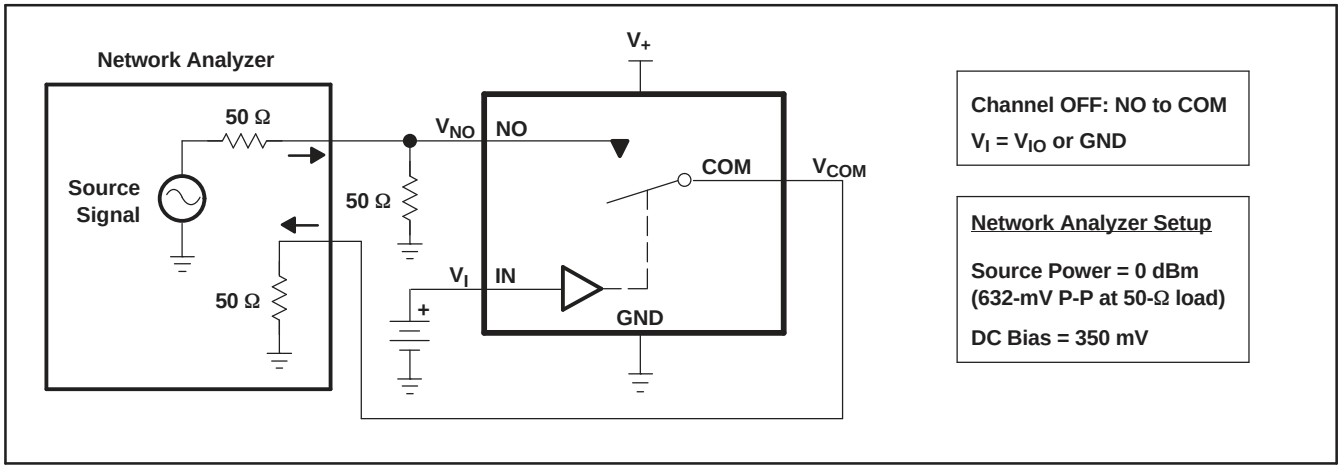


Figure 21. OFF Isolation (O_{ISO})

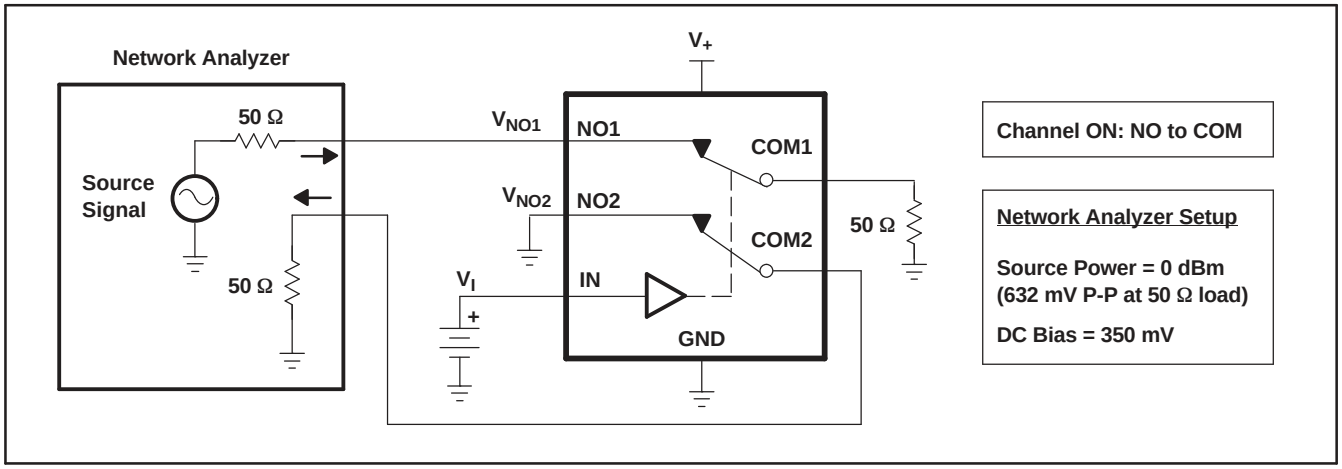
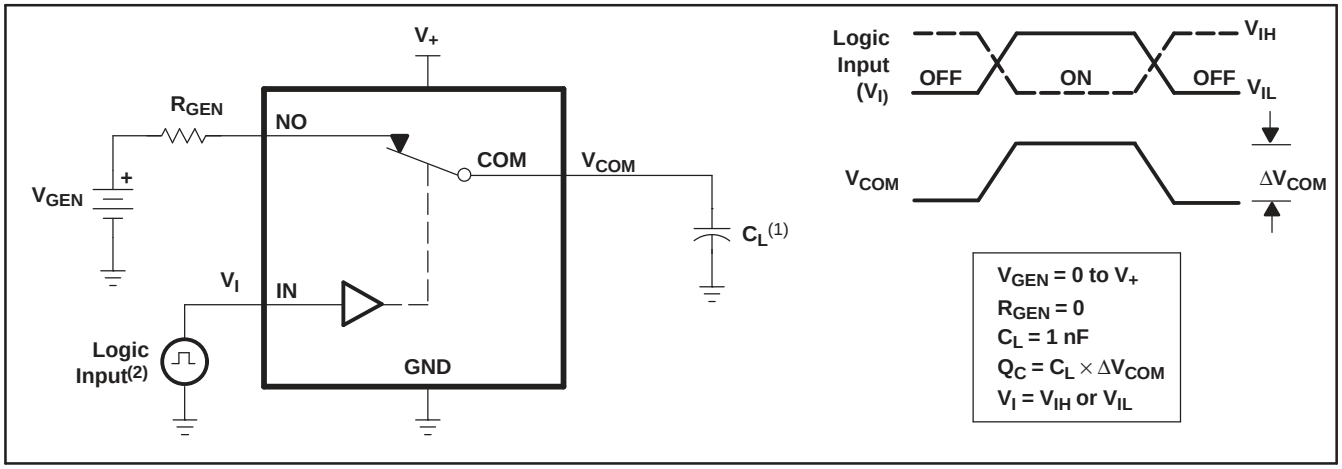


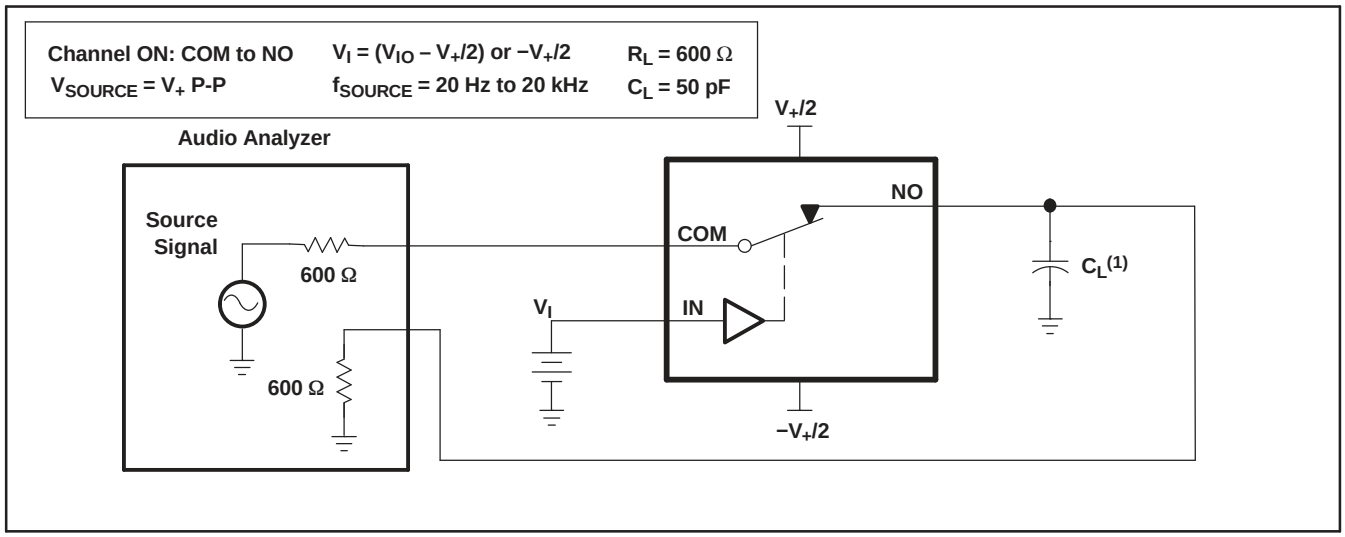
Figure 22. Crosstalk (X_{TALK})

PARAMETER MEASUREMENT INFORMATION (continued)



(1) C_L includes probe and jig capacitance.
(2) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

Figure 23. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 24. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A6542YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	JHN	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

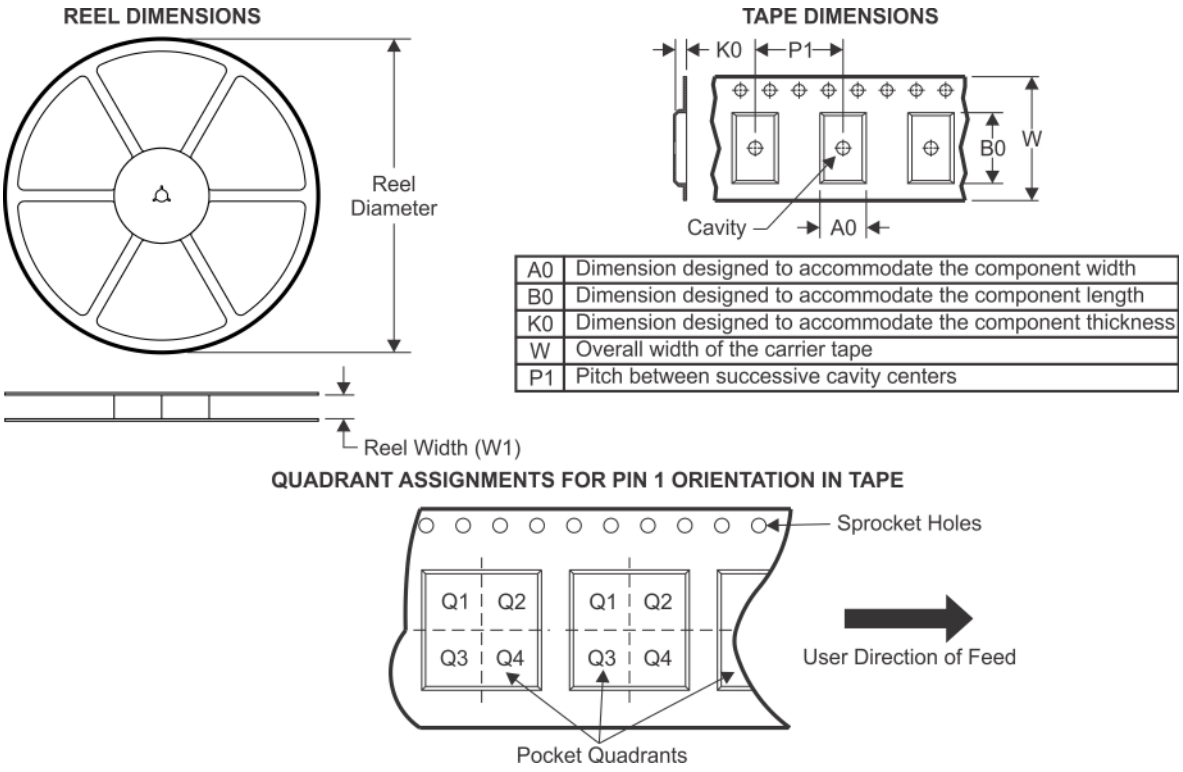
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

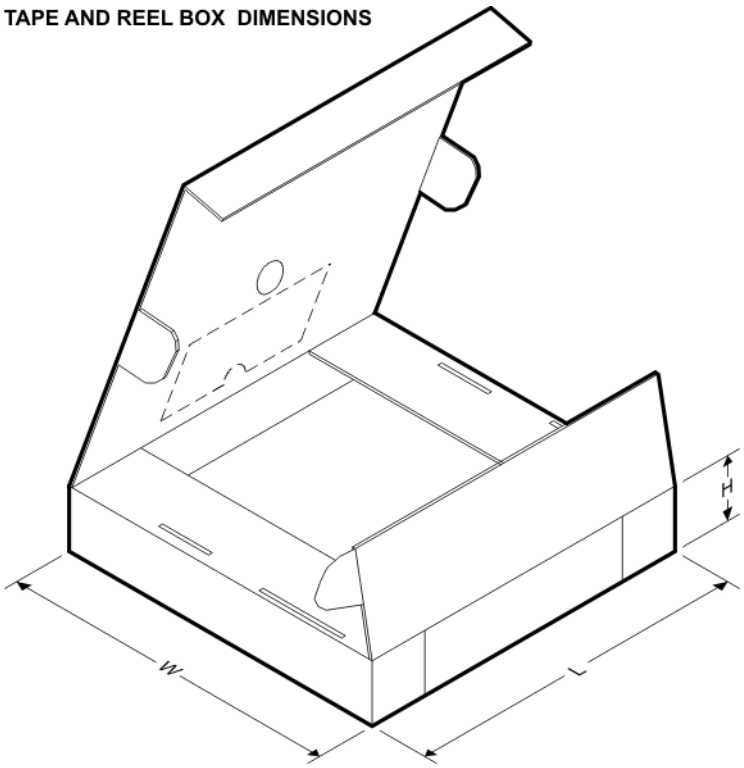


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A6542YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

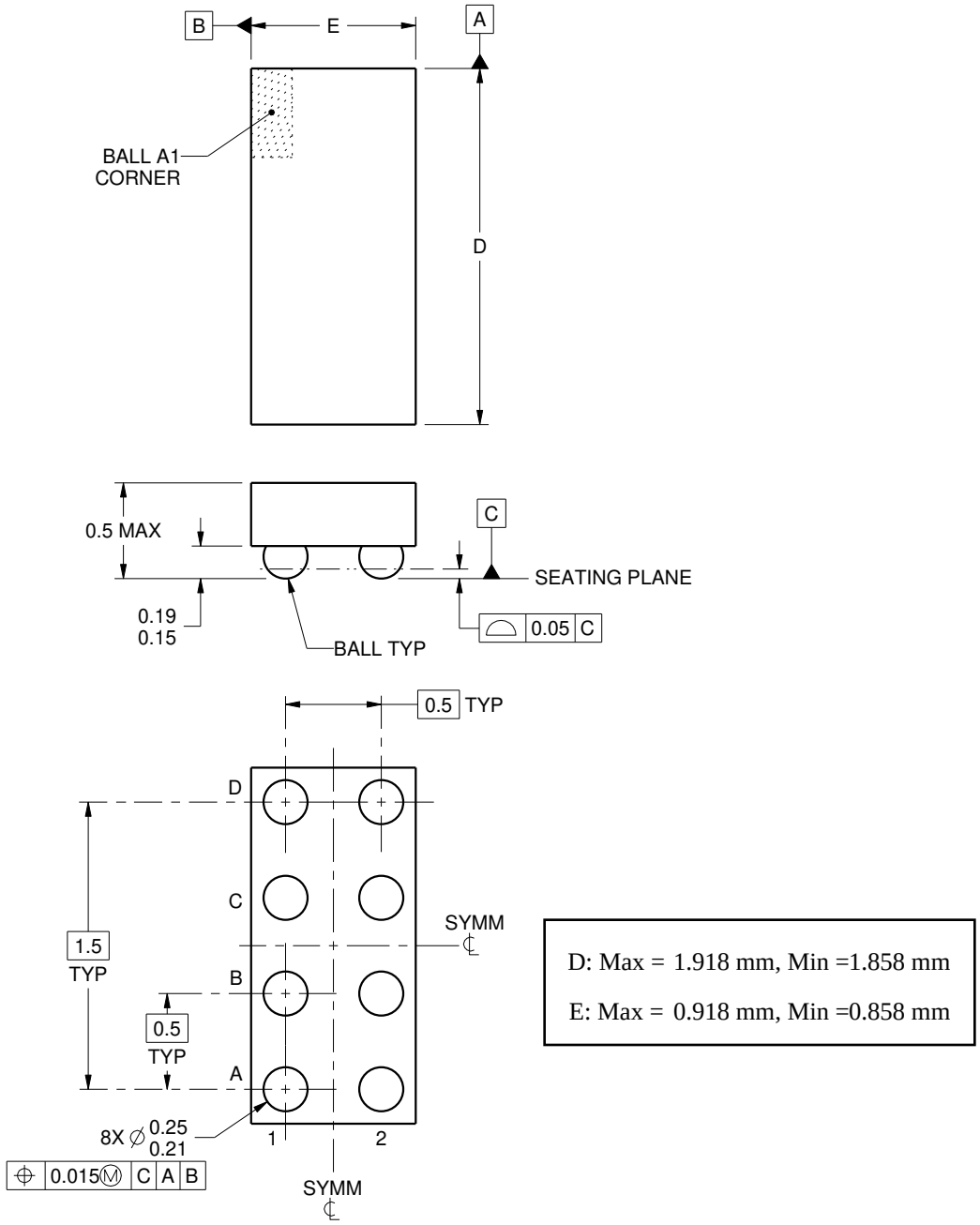
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A6542YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

PACKAGE OUTLINE

YZP0008

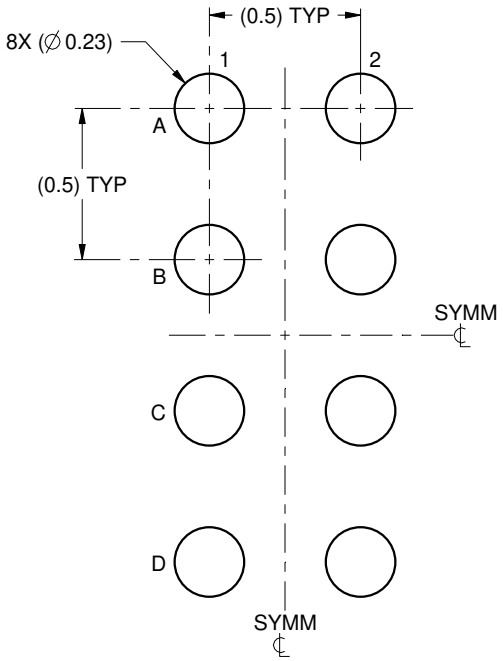
DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY

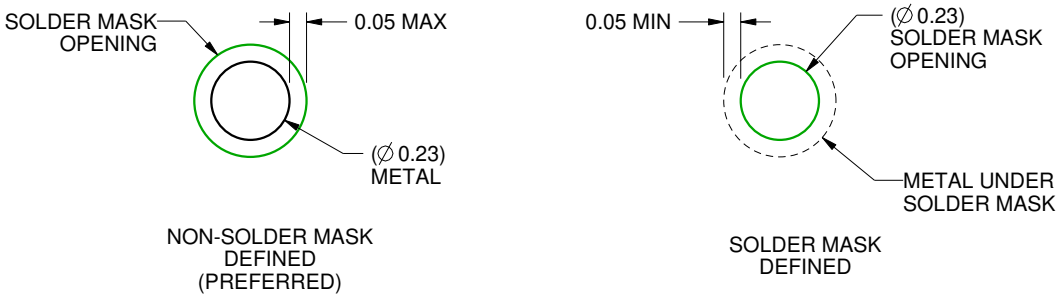


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X

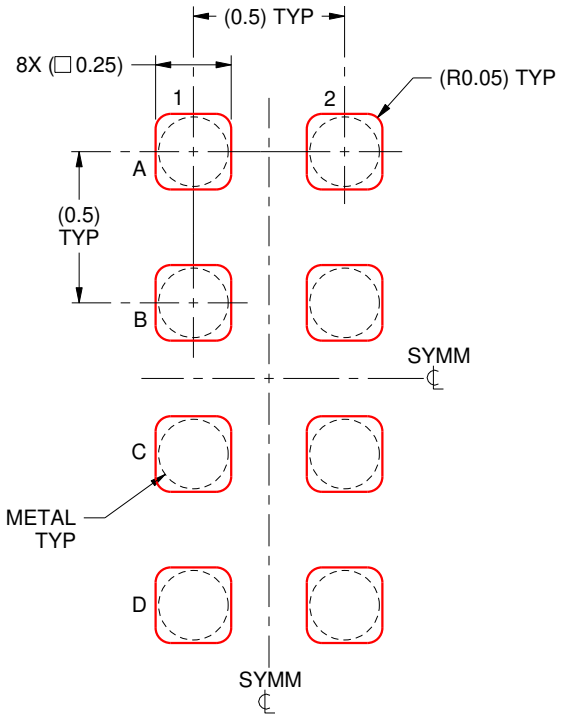


SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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